



JPW

PATENT
P57002

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

TAE-SUNG KIM *et al.*

Serial No.: 10/767,281

Examiner: WARREN, MATTHEW E

Filed: 30 January 2004

Art Unit: 2815

For: NOVEL CONDUCTIVE ELEMENTS FOR THIN FILM TRANSISTORS USED IN
A FLAT PANEL DISPLAY

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

In accordance with 37 C.F.R. §1.56, and §§1.97 and 1.98 as amended, Applicant cites, describes, and provides copies of the following art references. Under 37 C.F.R. §1.98(a)(2) however, copies of U.S. patent reference(s) are not provided.

FOREIGN PATENT REFERENCE(S):

- Japanese Patent Publication No. 2001-250956 to Koyama *et al.*, entitled *SEMICONDUCTOR DEVICE*, published on 14 September 2001.

Folio: P57002
Date: 9/14/06
I.D.: REB/ny

OTHER DOCUMENT:

- *Office action* from the Japanese Patent Office issued in Applicant's corresponding Japanese Patent Application No. 2004-066092 dated 5 September 2006.

DISCUSSION


As written in the Office action issued by the Japanese Patent Office on the 5 September 2006 in applicant's corresponding Japanese Application corresponding to applicant's above-captioned U.S. Patent Application, **Koyama et al.'JP956** discloses that to prevent alkaline metal ions in a glass substrate from being mixed into an active layer due to a gate voltage, thereby deteriorating an electric characteristic, a blocking layer obtained by laminating a nitride oxide silicon film (A) having a thickness of 50-100 nm and an oxynitride silicon film (B) having a thickness of 30-70 nm which have different composition ratios of oxygen and nitrogen, is provided on a back channel side of a TFT. The thickness of the oxynitride silicon film (B), which is greatly affected in particular, is made precise.

The citation of the foregoing references is not intended to constitute an assertion that other or more relevant art does not exist. Accordingly, the Examiner is requested to make a wide-ranging and thorough search of the relevant art.

Pursuant to 37 CFR § 1.97(d), the undersigned attorney hereby certifies that each item of information contained in this Information Disclosure Statement was cited in a communication from a foreign patent office in a counterpart foreign patent application not more than three(3) months prior to the filing of the statement.

No fee is incurred by this Statement.

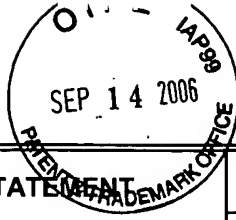
Respectfully submitted,



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INFORMATION DISCLOSURE STATEMENT
PTO-1449 (PAGE 1 OF 1)

SERIAL NUMBER 10/767,281

DOCKET NO. P57002

APPLICANT

TAE-SUNG KIM *et al.*

FILING DATE 30 January 2004

GROUP

2815

U.S. PATENT DOCUMENTS

EXAMINER	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE

FOREIGN PATENT DOCUMENTS

TRANSLATION

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	YES	NO
	JP 2001-250956	9/14/01	JAPAN			Abstract	

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

	<i>Office action</i> from the Japanese Patent Office issued in Applicant's corresponding Japanese Patent Application No. 2004-066092 dated 5 September 2006

EXAMINER:

DATE CONSIDERED:

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP §609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.